1. General description

PNP high power bipolar transistor in a power SOT1289B (CFP15B) flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: MJPE44H11

2. Features and benefits

- High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- · Electrically similar to popular MJD45H series
- Low collector emitter saturation voltage

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Constant current drive backlighting application
- Motor drive
- · Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-80	V
I _C	collector current		-	-	-8	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-16	Α
h _{FE}	DC current gain	V_{CE} = -1 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	60	-	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	5	C
2	В	base		В—
3	С	collector		
			CFP15B (SOT1289B)	E sym132

6. Ordering information

Table 3. Ordering information

Type number Package						
	Name	Description	Version			
MJPE45H11		plastic, thermal enhanced ultra thin SMD package; 3 leads; 2.13 mm pitch; 5.8 x 4.3 x 0.95 mm body	SOT1289B			

7. Marking

Table 4. Marking codes

Type number	Marking code
MJPE45H11	JPE45H11

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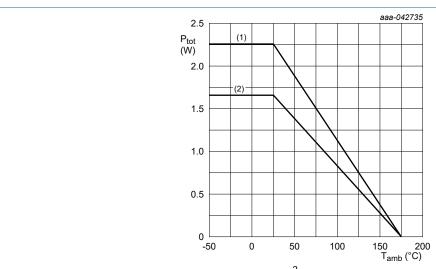
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-80	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-8	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-16	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.65	W
			[2]	-	2.25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 µm single-sided copper, standard footprint.
- 2] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 μm single-sided copper, mounting pad for collector 1 cm².



- (1) FR4 PCB, single-sided 140 µm copper, 1 cm²
- (2) FR4 PCB, single-sided 140 µm copper, standard footprint

Fig. 1. Power derating curves

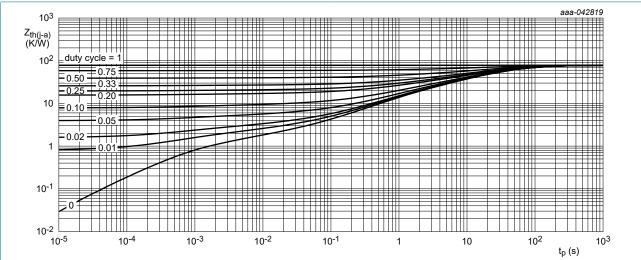
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9. Thermal characteristics

Table 6. Thermal characteristics

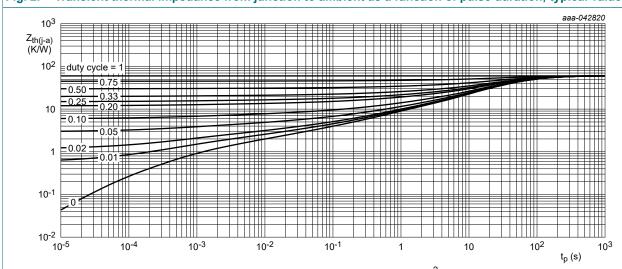
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	91	K/W
junction to	junction to ambient	ambient	[2]	-	-	67	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	3	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 µm single-sided copper, standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 μm single-sided copper, mounting pad for collector 1cm².



FR4 PCB, single-sided 140 µm copper, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided 140 µm copper, mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

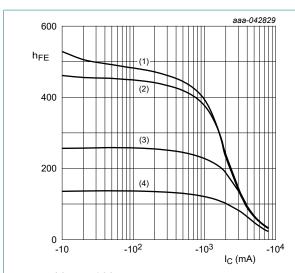
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = -2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-80	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = -100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	-6	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = -64 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-1	μΑ
I _{CES}	collector-emitter cut-off	V _{CE} = -64 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-1	μΑ
	current	V _{CE} = -64 V; V _{BE} = 0 V; T _j = 150 °C	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-1	μΑ
h _{FE}	DC current gain	V_{CE} = -1 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	60	-	-	
		V_{CE} = -1 V; I_{C} = -4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -8 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1	V
V _{BEsat}	base-emitter saturation voltage	I_C = -8 A; I_B = -800 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.5	V
t _{on}	turn-on time	I _C = -5 A; I _{Bon} = -0.5 A; I _{Boff} = 0.5 A;	-	250	-	ns
t _s	storage time	V _{CC} = -12.5 V; T _{amb} = 25 °C	-	245	-	ns
t _f	fall time		-	120	-	ns
t _{off}	turn-off time		-	370	-	ns
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	85	-	pF
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -500 mA; f = 100 MHz; T_{amb} = 25 °C	-	90	-	MHz

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$$V_{CE} = -1 V$$

$$(1) T_{amb} = 175 °C$$

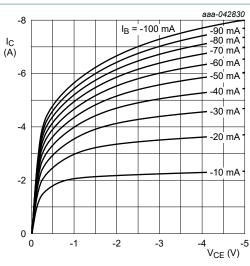
(2)
$$T_{amb} = 150 \,^{\circ}\text{C}$$

(3) $T_{amb} = 25 \,^{\circ}\text{C}$
(4) $T_{amb} = -55 \,^{\circ}\text{C}$

(3)
$$T_{amb} = 25 \, ^{\circ}C$$

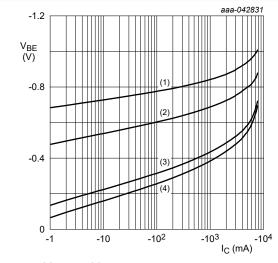
$$(4) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $V_{CE} = -5 V$

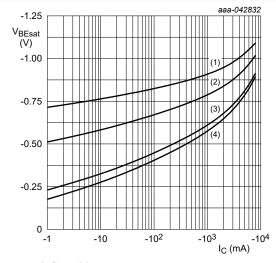
$$(1) T_{amb} = -55 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

(4)
$$T_{amb} = 175 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

$$(1) T_{amb} = -55 °C$$

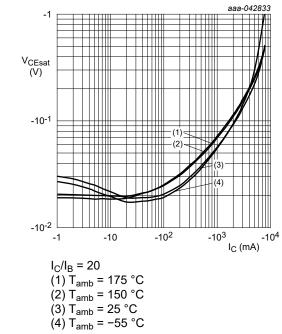
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

(3)
$$T_{amb} = 175 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

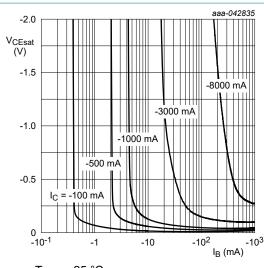
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(3)
$$T_{amb} = 25 \, ^{\circ}C$$

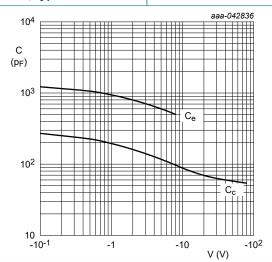
$$(4) T_{amb} = -55 °C$$

Collector-emitter saturation voltage as a Fig. 8. function of collector current; typical values



 T_{amb} = 25 °C

Fig. 9. Collector-emitter saturation region as a function of base current; typical values

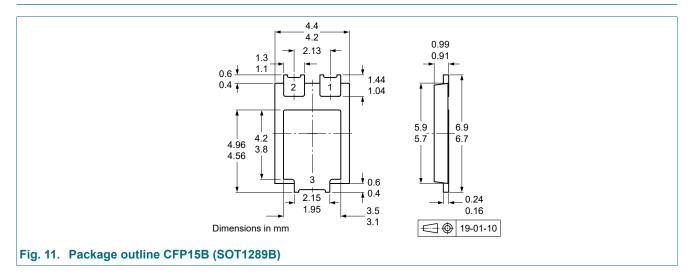


 $T_{amb} = 25 \, ^{\circ}C$

Fig. 10. Input/output capacitance as a function of input/output voltage

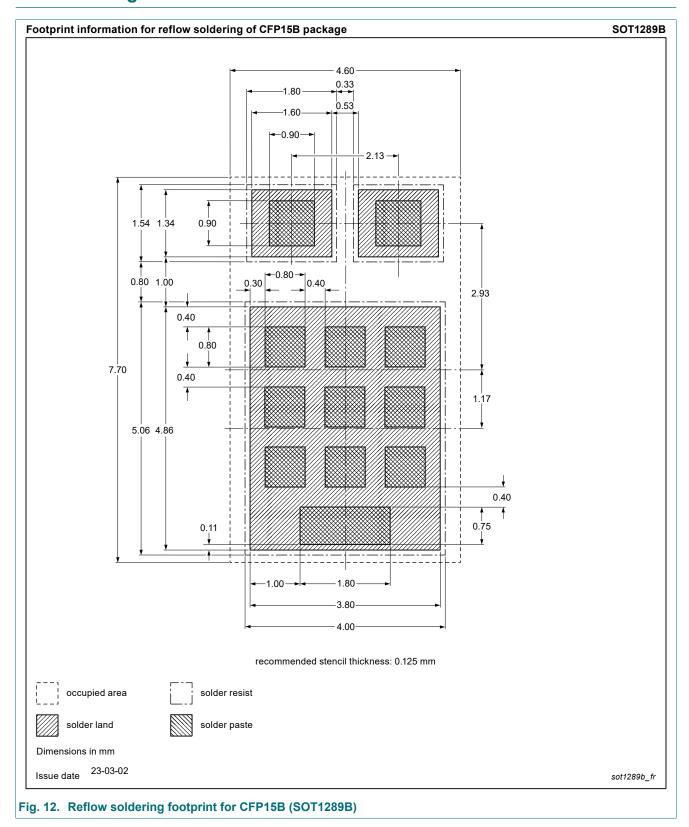
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11. Package outline



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12. Soldering



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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
MJPE45H11 v.1	20250422	Product data sheet	-	-

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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